

crystal growth direction which is parallel to the insulating surface;

an insulating film on the crystalline semiconductor film;

A1
Cont'd
a plurality of electrodes being formed on the insulating film, each of said plurality of electrodes being located within a predetermined distance so that a plurality of MOS capacitors are formed between the plurality of electrodes and the crystalline semiconductor film with the insulating film therebetween,

wherein a charge is transferred from one of the MOS capacitors to another of the MOS capacitors in a charge transfer direction,

wherein said charge transfer direction is aligned with said crystal growth direction.

17. (New) A device according to claim 16, wherein said insulating surface is a quartz substrate.

18. (New) A device according to claim 16, wherein said semiconductor device is at least one selected from the group consisting of an image sensor, a delay line, a filter, a memory and an operation unit.

19. (New) A semiconductor device comprising:
a photoelectric conversion being formed over an
insulating surface;
a charge coupled device being electrically connected to
the photoelectric conversion device and formed over the
insulating surface;
said charge coupled device including:
a crystalline semiconductor film being formed on
the insulating surface, said crystalline semiconductor film
having a crystal growth direction which is parallel to the
insulating surface;
an insulating film on the crystalline
semiconductor film;
a plurality of electrodes being formed on the
insulating film, each of said plurality of electrodes being
located within a predetermined distance so that a plurality of
MOS capacitors are formed between the plurality of electrodes and
the crystalline semiconductor film with the insulating film
therebetween,
wherein a charge is transferred from one of the MOS
capacitors to another of the MOS capacitors in a charge transfer
direction,

wherein said charge transfer direction is aligned with said crystal growth direction.

20. (New) A device according to claim 19, wherein said insulating surface is a quartz substrate.

21. (New) A device according to claim 19, wherein said semiconductor device is an image sensor.

22. (New) A device according to claim 19, wherein said photoelectric conversion device is a photodiode.

23. (New) A device according to claim 19 further comprising an active matrix type liquid crystal display device being integrated over the insulating surface.

REMARKS

Reconsideration and allowance of the above-referenced application are respectfully requested. After entry of this amendment, claims 1-6, 11-14, and 16-23 will be pending.

Applicant acknowledges the election without traverse to prosecute claims 1-6 and 11-14 as noted in the official action.